

REMARKS/ARGUMENTS

Claim 9 has been rejected under 35 U.S.C. §103(a) over Davies in view of Ajit et al. It has been set forth that Davies teaches, among other limitations of claim 9, using the stripes of oxide and polysilicon for forming the second base diffusions as set forth in claim 9. It is respectfully submitted that Davies does not teach using the oxide and polysilicon stripes in forming the second base diffusions. Indeed, Davies teaches the opposite.

Davies teaches forming sidewall spacers 18 before forming low resistivity regions 17. That is, sidewall spacers 18 are used for positioning low resistivity regions. Col. 4, line 12-14.

Davies teaches that using the sidewall spacers 18 is critical in manufacturing his device:

Width of sidewall spacer 18 is a critical feature of the present invention, and is determined by thickness of the deposited layer from which sidewall spacer 18 was etched. In a preferred embodiment, spacer 18 is about as wide as thickness of polysilicon gate 14, or about 0.3-0.8 microns. Thinner spacer width corresponds to smaller source depth for optimal performance, thus actual thickness is a design choice based on diffusion and film deposition technology. Width of sidewall spacer 18 determines relative spacing between source 15, base 12, and low resistivity region 17. If this spacing is too small, or varies widely due to the process control of forming spacer 18, low resistivity region 17 will extend into channel 26, destroying the device. For example, it has been found that if a thin oxide, analogous to oxide 15 shown in FIG. 1, is used rather than a sidewall spacer 18, insufficient separation between base 12 and low resistivity region 17 is provided, and correspondingly low yields result.
Col. 4, lines 25-43.

The excerpt noted above indicates that Davies actually teaches away from using the oxide and polysilicon stripes as a mask in forming the second base regions (low resistivity regions 17). It is respectfully submitted, therefore, that Davies does not teach or suggest using the oxide and polysilicon stripes as a mask for forming the second based diffusions. Reconsideration is requested.

Claims 10-14 depend from claim 9, and, therefore, include the limitations of claim 9. Each of these claims includes additional limitations which in combination with those of claim 9 are not shown or suggested by the art of record. Reconsideration is requested.

The application is believed to be in condition for allowance. Such action is earnestly solicited.

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on June 6, 2003:

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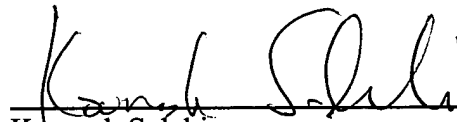
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Signature

June 6, 2003

Date of Signature

Respectfully submitted,



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